

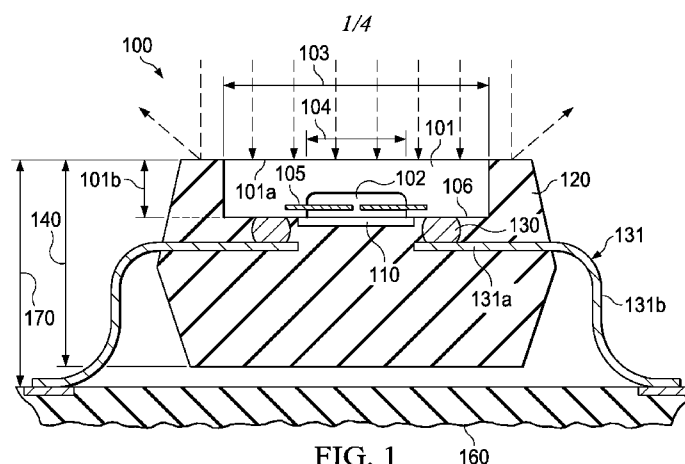


- (51) **International Patent Classification:**
B81B 7/00 (2006.01) *H01L 23/00* (2006.01)
B81B 3/00 (2006.01)
- (21) **International Application Number:**
PCT/US2013/049516
- (22) **International Filing Date:**
8 July 2013 (08.07.2013)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
13/542,827 6 July 2012 (06.07.2012) US
- (63) **Related by continuation (CON) or continuation-in-part (CIP) to earlier application:**
US 13/542,827 (CON)
Filed on 6 July 2012 (06.07.2012)
- (71) **Applicant: TEXAS INSTRUMENTS INCORPORATED** [US/US]; P.O. Box 655474, Mail Station 3999, Dallas, TX 75265-5474 (US).
- (71) **Applicant (for JP only): TEXAS INSTRUMENTS JAPAN LIMITED** [JP/JP]; 24-1, Nishi-Shinjuku 6-chome, Shinjuku-ku Tokyo, 160-8366 (JP).
- (72) **Inventor: KODURI, Sreenivasan.**; 2023 Burnside Dr., Allen, TX 75013 (US).
- (74) **Agent: FRANZ, Warren L.**; Texas Instruments Incorporated, P.O. Box 655474, Mail Station 3999, Dallas, TX 75265-5474 (US).
- (81) **Designated States** (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.
- (84) **Designated States** (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))
- as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))

[Continued on next page]

(54) **Title:** SENSOR MEMS DEVICE CANTILEVER PACKAGING**FIG. 1**

(57) **Abstract:** A packaged sensor MEMS (100) has a semiconductor chip (101) with a protected cavity (102) including a sensor (105), the cavity surrounded by solder bumps (130) attached to the chip terminals; further a leadframe with elongated and radially positioned leads (131), the central lead ends (131a) attached to the bumps. Insulating material (120) encapsulates chip and central lead ends, leaving the chip surface (101a) opposite the cavity and the peripheral lead ends (131b) unencapsulated. The unencapsulated peripheral lead ends are bent into cantilevers for attachment to a horizontal substrate (160), the cantilevers having a geometry to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics, especially when supported by lead portions with curved, toroidal, or multiple-bendings geometries.



Published:

— with international search report (Art. 21(3))

— before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments (Rule 48.2(h))

SENSOR MEMS DEVICE CANTILEVER PACKAGING

[0001] This relates to semiconductor devices and their fabrication, especially microelectromechanical system (MEMS) devices in gull-wing packages suitable for sensors and other industrial applications.

BACKGROUND

[0002] The wide variety of products collectively called microelectromechanical system (MEMS) devices are small, low weight devices on the micrometer to millimeter scale, which may have mechanically moving parts and often movable electrical power supplies and controls, or they may have parts sensitive to thermal, acoustic, or optical energy. MEMS devices have been developed to sense mechanical, thermal, chemical, radiant, magnetic, and biological quantities and inputs, and produce signals as outputs. Because of the moving and sensitive parts, MEMS devices have a need for physical and atmospheric protection. Consequently, MEMS devices are placed on or in a substrate and have to be surrounded by a housing or package, which has to shield the MEMS against ambient and electrical disturbances, and against stress.

[0003] A microelectromechanical system (MEMS) device integrates mechanical elements, sensors, actuators, and electronics on a common substrate. The manufacturing approach of such a device aims at using batch fabrication techniques similar to those used for microelectronics devices. MEMS devices can thus benefit from mass production and minimized material consumption to lower the manufacturing cost, while trying to exploit the well-controlled integrated circuit technology.

[0004] An example of MEMS includes mechanical sensors, both pressure sensors including microphone membranes, and inertial sensors such as accelerometers

coupled with the integrated electronic circuit of the chip. The mechanically moving parts of a MEMS are fabricated together with the sensors and actuators in the process flow of the electronic integrated circuit (IC) on a semiconductor chip. The mechanically moving parts may be produced by an undercutting etch at some step during the IC fabrication; examples of specific bulk micromachining processes employed in MEMS sensor production to create the movable elements and the cavities for their movements are anisotropic wet etching and deep reactive ion etching.

[0005] Another example is an 8-pin digital infrared (IR) temperature sensor made in a silicon chip of about 2 by 2 mm side length, which includes a thermopile (multiple thermo-elements) of bismuth/antimony or constantan/copper pairs on a sensor membrane suspended in a cavity created by anisotropic silicon wet etching through a grid of holes (hole diameter about 18 μm , hole pitch about 36 μm center-to-center) in the membrane. The cavity is closed by a laminate cover-plate (about 14 μm thick) overlaying the membrane to protect the sensors, and the IR radiation reaches the thermocouple tips through the rear silicon bulk of the cavity. The resulting hot spot on the thermocouple tips creates a temperature difference between the tips and the opposite thermocouple ends at ambient temperature, which in turn creates the voltage difference to be monitored as a contactless temperature measurement. For the 8 pins, the chip may have 8 solder bumps surrounding the cover plate-protected cavity or 8 pressure contacts and is thus commonly referred to as a wafer-chip-scale package (WCSP); in the modification with pressure (or solderable) contacts, the package belongs to the quad flat no-lead (QFN) family.

SUMMARY

[0006] Embodiments of a MEMS device are described such as a sensor that enables reliable and cost-effective encapsulation in a housing giving unobstructed access by a physical parameter (light, sound, gas, moisture) to be monitored and absorbing thermo-mechanical stress and environmental vibrations.

[0007] In an example sensor MEMS device, a semiconductor chip has a surface with a protected cavity containing the sensor and a plurality of solder bumps of the chip terminals surrounding the cavity. When an industrial application of a

MEMS device assembled on a board involves wide and abrupt temperature swings, significant thermo-mechanical stresses are caused due to widely different coefficients of thermal expansion between the silicon-based sensor and the material of the board. These stresses are sufficient to induce micro-cracks in the attached solder bumps, leading to fracture failures.

[0008] For protecting the MEMS device against stress-induced failures, a MEMS package having elastic cantilever leads acts as a stress-absorbing compliant barrier between the silicon-based MEMS and the external environment.

[0009] Suitable packages have cantilever leads protruding from the package, which can accommodate, under a force lying in the plane of the expanding and contracting substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent lead material characteristics. Such elastic cantilever properties can be achieved by cantilever geometries, which may be selected from straight geometry, curved geometry, toroidal geometry, and multiple-bendings geometry.

[0010] Unobstructed access to the MEMS sensor and the elastic cantilever leads of the package are simultaneously accomplished when the central lead portions of the leadframe match the chip solder bumps so that the bumps can be attached to the central lead ends and then encapsulated, while the chip surface opposite the cavity with the sensor remains unencapsulated. The peripheral lead portions also remain unencapsulated when insulating material encapsulates the MEMS chip and the central lead ends; since these lead portions protrude as cantilevers from the package, they may be formed so that the cantilevers operate as springs to absorb thermo-mechanical stresses.

[0011] In one embodiment, the bump-studded MEMS chip are implemented in a pre-fabricated plastic housing with the leadframe integrated into the housing. The housing is made of an insulating material shaped in small-outline configuration and preferably has a central recess of a depth greater than the chip height with bumps. The leadframe has elongated and radially positioned leads with the central lead ends matching the chip solder bumps and positioned on the bottom of the recess, and the peripheral lead ends protruding from the housing. In a solder reflow step, the chip

solder bumps are attached to the leadframe so that the recess depth is equal to or surpasses the bumped chip height. When the protruding lead ends are bent into cantilevers for attachment to a horizontal substrate, the cantilevers having a geometry to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics.

BRIEF DESCRIPTION OF THE DRAWINGS

[0012] FIG. 1 shows a cross section of an example radiation-sensing MEMS device assembled in a package with stress-absorbing cantilever leads.

[0013] FIG. 2A shows an enlarged cross section OF a portion of the MEMS sensor of FIG. 1.

[0014] FIG. 2B is a bottom view of the MEMS sensor, before the MEMS solder balls are attached to the central lead ends.

[0015] FIG. 3 is a top view of an example device.

[0016] FIGS. 4 to 7 illustrate examples of straight, toroidal, curved and multiple bending lead geometries respectively for the peripheral lead ends protruding from the package.

[0017] FIG. 8 shows a cross section of an example radiation-sensing MEMS device assembled in a package with stress-absorbing cantilever leads, wherein the package has a recess of a depth greater than the assembled chip height.

[0018] FIG. 9 illustrates a cross section of the example radiation-sensing MEMS device of FIG. 8 with an iris attached to the sidewalls of the package recess.

DETAILED DESCRIPTION OF EXAMPLE EMBODIMENTS

[0019] FIG. 1 illustrates an example MEMS device embodiment 100. The device includes a semiconductor chip 101 with terminals 106; chip 101 is embedded in an insulating package 120. Chip 101 contains a cavity 102 with a microelectromechanical system (MEMS) 105. An example chip suitable as an infrared-sensing MEMS may be square-shaped with a side length 103 of about 2 mm. The terminals of chip 101 are attached by solder bumps 130 to package leads 131, which are formed as cantilever leads. The plurality of cantilever leads 131 of package 120 are interconnected, preferably by solder, to external parts such as

substrate 160. While thickness 101b of chip 101 may be in the range between 0.2 and 0.3 mm, the height 140 of package 120 may be any standard thickness of SOIC devices; as an example, the height 170 of package 120 together with bent leads 131 may be approximately 1 mm. Package 120 is preferably made of an insulating plastic or ceramic compound; the package encapsulates chip 101 and the central lead ends 131a, leaving the chip surface 101a opposite the cavity 102 and the peripheral lead ends 131b unencapsulated.

[0020] The material of substrate 160, while generally insulating, depends on the application of device 100; as an example of the application, infrared-sending MEMS are used in ever increasing numbers for industrial purposes such as automotive and household applications. These applications are characterized by wide and often rapid temperature swings, for instance from sub-zero temperatures to more temperatures well above 100 °C. In order to keep the cost of sensor MEMS low, preferred substrate selections for industrial applications include plastic and ceramic materials. Given the wide temperature variations in industrial applications, the selection of plastic and ceramic materials for substrate 160 represents a challenge for the reliability of the sensor MEMS devices 100 due to the thermo-mechanical stress caused by the much higher coefficient of thermal expansion (CTE) of the substrate materials compared to the CTE of the silicon chip 101 of the MEMS (typically about one order of magnitude or more). The methodology to construct the cantilever leads 131 as stress-absorbing compliant barriers between the silicon-based MEMS and the substrate 160 is discussed below.

[0021] Chip 101 has the opening 104 of cavity 102 facing away from the surface 101a of chip 101 and the top side of device 100. In the example embodiment of FIG. 1, located inside cavity 102 is MEMS 105, preferably a radiation sensor. Example sensors may be selected from a group responsive to electromagnetic radiation, such as visible or infrared light. A preferred example as sensor in FIG. 1 is a digital infrared (IR) temperature sensor including a thermopile (multiple thermo-elements) of bismuth/antimony or constantan/copper pairs on a sensor membrane 105. The membrane is suspended in cavity 102 created by anisotropic silicon wet

etching through a grid of holes (hole diameter about 18 μm , hole pitch about 36 μm center-to-center) in the membrane.

[0022] In an enlarged view, FIG. 2A shows the surface 101a of MEMS chip 101 is coplanar with surface 120a of package 120. Opposite surface 101a, the opening of cavity 102 of the MEMS chip is closed by a laminate cover-plate 110 (about 15 μm thick) overlaying the membrane 105 to protect the sensors. The plate, for instance made of cured photoresist, is transmissive to the radiation sensed by the MEMS. It should be pointed out that cover plate 110 not only needs to seal cavity 102, but also needs to provide thermal isolation of the MEMS relative to encapsulation compound 120. Such thermal isolation prevents the temperature sensor 105 from being thermally shortened to encapsulation compound 120. As a consequence, a thermally shielding additional layer may have to be added to plate 110; alternatively, a pocket of reduced atmospheric pressure, such an additional cavity, may have to be added to layer 120.

[0023] In the example of FIG. 2A, the IR radiation 150 reaches the center area of the thermocouples, which have been formed from the membrane 105. On the way, radiation 150 traverses the bulk of semiconductor chip 101, which may act as a filter. Due to the incoming radiation 150, a hot spot on the thermocouple tips creates a temperature difference between the tips and the opposite thermocouple ends, which retain ambient temperature. The resulting temperature difference is marked in FIG. 2A by ΔT . The temperature difference in the thermocouples creates the voltage difference to be monitored as a contactless temperature measurement.

[0024] FIG. 2B illustrates a bottom view of example chip 101, before the chip is assembled in the package. Example chip 101 is square-shaped with side length 101c of about 2 mm and has a window to cavity 102 with a side length 102a of about 0.4 mm. Solder balls 130 are attached to the plurality of terminals of MEMS chip 101 (the terminals being preferably copper pads). In conventional usage, solder balls 130 would be directly attached to a substrate. Consequently, thermo-mechanical stresses due to the mismatch of CTEs of substrate and semiconductor chip have to be absorbed directly by the attached solder balls. Experience has shown that the solder

balls have a high probability of fatiguing, in some applications after only relatively few temperature cycles and then developing solder microcracks.

[0025] A leadframe with elongated leads 131 is provided. The leadframe is stamped or etched from a base sheet metal selected from, but not limited to, copper, copper alloy, aluminum, iron-nickel alloy, or Kovar™; preferred thicknesses of the base material are from about 0,15 to 0.25 mm. The central leadframe portions have a metallurgical surface suitable for adhesion to plastic or ceramic compounds used as material for package 120, especially to molding compounds. The peripheral leadframe portions protrude from the package and have a metallurgical surface suitable for attachment to external parts 160, preferably using a solder technology. As FIG. 3 shows, the central lead ends 131a are flat and matching the solder balls 130 of chip 101 so that they can be attached to the solder balls; in a general sense, the central leads may be considered radially positioned. The outer lead ends 131b include the elongated cantilever portion of leads 131 whereby the outer ends 131b can be formed in three-dimensional fashion for instance as gull-wings (see FIG. 1) or as J-leads.

[0026] When an industrial application of a MEMS assembled on a board involves wide and abrupt temperature swings, significant thermo-mechanical stresses may be caused due to widely different coefficients of thermal expansion between the silicon-based sensor and the material of the board. The MEMS device can be protected against stress-induced failures, when the MEMS package has elastic cantilever leads acting as stress-absorbing compliant barriers between the silicon-based MEMS device and the external environment.

[0027] Suitable packages, such as depicted in the example device of FIG. 1, have cantilever leads protruding from the package, which can accommodate, under a force lying in the plane of the expanding and contracting substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent lead material characteristics. Such elastic cantilever properties can be achieved by cantilever geometries, which may be selected from leads with straight geometry, curved geometry, toroidal geometry, and multiple-bendings geometry.

[0028] For a lead protruding from the package in straight lead geometry, as depicted by lead 431 of FIG. 4, the process step of forming the lead uses a force, which has a vertical component causing the bending, and a horizontal component causing the elongation. The outside force, applied along the length of the lead 431, stretches the lead in the direction of the length, while the dimension of the width is only slightly reduced, so that the new shape appears slightly elongated. For elongations small (i.e. less than 8 %) compared to the length, and up to a limit, called the elastic limit given by the material characteristics, the amount of elongation is linearly proportional to the force. Beyond that elastic limit, the segment would suffer irreversible changes and damage to its inner strength and may eventually break. The resulting unencapsulated peripheral lead ends are bent into cantilevers suitable for attachment to a horizontal substrate, as depicted in example FIG. 1. As shown in FIGS. 4 to 7, the cantilevers have a geometry to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics. When attached to a horizontal substrate, the package leads are suitable to act as spring-like compliant cantilevers.

[0029] FIG. 4 indicates the elongation-only approach. Tip 431c of lead 431 is attached to a substrate. The solid line represents the lead configuration at ambient temperature. At elevated temperatures, the substrate expands due to its high CTE and exerts force aiming at elongating lead 431 by a small fraction designated 431d.

[0030] The two-fold approach substituting for an elongation-only solution (FIG. 4) includes linearizing a design in bending, and stretching through pulling (FIGS. 5 to 7). The contribution of linearizing can be obtained when a topologically long body is first designed so that it contains curves, bendings, meanderings or similar non-linearities. By applying force, at least part of the non-linearities is stretched or straightened so that afterwards the body is elongated. This can be visualized in the familiar action that an arm, angled at the elbow, will be lengthened when the lower arm is stretched to get in line with the upper arm.

[0031] The contribution of stretching is similar to the elongation in the direction of the lead length discussed above. This stretching, therefore, will remain

safely below the elastic limit of the leadframe material. The nature and effect of both contributions will become more readily understood from the following description of the illustrations FIGS. 5 to 7. In all examples, the tips of the leads are attached to a substrate with high CTE. At elevated temperatures, the expanding substrate exerts force aiming at pulling at the lead. In FIG. 5, toroids are shown by straight lines in their original stamped, or etched, design before the pulling process, and by dashed lines in their final shape after the pulling process. The contribution for achieving the additional length of the leads from straightening the designed-in curved shape of the toroids is evident.

[0032] In FIGS. 6 and 7, the leads together with their bendings are shown by solid lines in their original (stamped or etched) design before the extension process, designated 631 and 731 respectively, and by dashed lines in their shapes after the extension process, designated 632 and 732 respectively. The significant contribution from the partial straightening the designed-in curved shape of the lead bendings is clearly visible for achieving the additional length of the lead.

[0033] With this designed-in capability of bending and stretching selected leadframe leads beyond the limit of simple elongation based upon inherent material characteristics, leadframes with spring-like leads can be manufactured for attachment to boards in industrial MEMS applications with elastic features for large and rapid temperature swings which cannot be achieved by solder bump attachments to boards.

[0034] An embodiment of a method for fabricating a sensor MEMS starts with the step of providing a semiconductor chip, which has a surface with a protected cavity containing a sensor. The cavity is surrounded by solder bumps attached to the chip terminals. A leadframe is provided, which has elongated and radially positioned leads; the central lead ends are solderable and match the chip solder bumps. In addition, the leads may have geometries selected from a group including straight geometry, curved geometry, toroidal geometry, and multiple bendings geometry.

[0035] In a next process step, the chip solder bumps are aligned to the central lead ends. The solder bumps are then reflowed, whereby the chip is attached to the leadframe. Thereafter, the chip and the central lead ends are encapsulated in an insulating material, leaving unencapsulated the chip surface opposite the cavity and

the peripheral lead ends. When the leads include portions with curved geometries, toroidal geometries, or multiple bendings geometries, those lead portions also remain unencapsulated. A preferred encapsulation method is a molding process using a polymeric compound.

[0036] In a later process step, the unencapsulated lead ends are bent into spring-like cantilevers. When these cantilever leads are attached to external parts like substrates and boards, preferably by soldering, they are able to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics.

[0037] Another embodiment is a packaged sensor MEMS device as illustrated in the example FIG. 8. The device, generally designated 800, includes a semiconductor chip 801, which has a lateral dimension 803 and a surface 801c with a cavity 802, protected by a cover plate 810. Cavity 802 contains a sensor 805. The cavity is surrounded by solder bumps 830, which are attached to the chip terminals. In FIG. 8, the height of the bumped chip is designated 880.

[0038] In contrast to the embodiment illustrated in FIGS. 1 and 2, the structure of the embodiment in FIG. 8 offers, with regard to cover plate 810, thermal isolation of plate 810 from encapsulation material 820. Consequently, no additional precaution for thermal isolation of plate 810 from material 820 is needed.

[0039] Device 800 further includes a package consisting of a housing 820 and a leadframe integrated in the housing. Housing 820 is made of an insulating material such as plastic or ceramic, preferably shaped in small-outline configuration. Housing 820 has lateral dimension 821 greater than chip dimension 803, and has a central recess of a depth 881 greater than the chip height 880. The leadframe has elongated and radially positioned leads 831 with the central lead ends solderable, matching the chip solder bumps 830 and positioned on the bottom of the recess; the peripheral lead ends 831b are protruding from the housing 820.

[0040] The chip solder bumps 830 are attached to the leadframe so that the recess depth 831 surpasses the bumped chip height 830. When the sidewalls of the recess surpass the surface 101a of chip 101, it has the technical advantage of constricting the amount of thermal radiation 850, which can impinge on chip 101;

excess radiation 851 is reflected away. Temperature measurements can thus be more localized and precise.

[0041] The protruding lead ends 831b are bent into cantilevers for attachment to a horizontal substrate 860; the cantilevers have a geometry to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics. As a consequence, the cantilevers act as springs able to absorb thermo-mechanical stress originating from the CTE difference between device 800 and substrate 860 and thus to act as a compliant barrier between the silicon-based MEMS and the external environment.

[0042] Even more localized and precise temperature measurements can be achieved by an embodiment displayed in FIG. 9 and generally designated 900. Device 900 has an iris 990 with opening 991 attached to the sidewalls of the recess in the package. Opening 991 narrows the incoming radiation to the constricted beam 950, while the balance 951 of the incoming radiation is reflected away by iris 990.

[0043] Another embodiment is a method for fabricating a MEMS with recessed sensor. The process starts with the step of providing a semiconductor chip, which has a surface with a protected cavity containing a sensor. The cavity is surrounded by solder bumps attached to the chip terminals. After attachment, the bumped chip has a height. A package is provided, which includes a housing and a leadframe integrated in the housing. The housing is made of an insulating material such as plastic or ceramic, and has preferably a small outline configuration. The housing further has a central recess of a depth greater than the height of the bumped chip.

[0044] The leadframe has elongated and radially positioned leads; the central lead ends are solderable and match the chip solder bumps. The central lead ends are positioned on the bottom of the recess, and the peripheral lead ends protrude from the housing. The peripheral leads have a geometry selected from a group including straight geometry, curved geometry, toroidal geometry, and multiple bendings geometry.

[0045] In A next process step, the chip solder bumps are aligned to the central lead ends. The solder bumps are then reflowed, whereby the chip is attached to the leadframe so that the recess depth surpasses the height of the bumped chip.

[0046] In a later process step, the peripheral leads, which protrude from the housing, are formed by bending into spring-like cantilevers. For some MEMS devices, the final process step is preceded by a process step, in which an iris is attached over the package recess in order to narrow the incoming radiation beam impinging on the sensor MEMS.

[0047] The described principles apply to products using any type of semiconductor chip, discrete or integrated circuit, and the material of the semiconductor chip may comprise silicon, silicon germanium, gallium arsenide, or any other semiconductor or compound material used in integrated circuit manufacturing.

[0048] The principles apply to MEMS devices having parts moving mechanically under the influence of an energy flow (acoustic, thermal, or optical), a temperature or voltage difference, or an external force or torque. Certain MEMS with a membrane, plate or beam can be used as a pressure sensor (for instance microphone and speaker), inertial sensor (for instance accelerometer), or capacitive sensor (for instance strain gauge and RF switch); other MEMS operate as movement sensors for displacement or tilt; bimetal membranes work as temperature sensors.

[0049] Those skilled in the art will appreciate that modifications may be made to the described embodiments and also that many other embodiments are possible within the scope of the claimed invention.

CLAIMS

What is claimed is:

1. A packaged sensor microelectromechanical system (MEMS) device, comprising:
 - a semiconductor chip having a surface with a protected cavity including a sensor, the cavity surrounded by solder bumps attached to the chip terminals;
 - a leadframe having elongated leads, the central lead ends matching the chip solder bumps and being attached to the bumps;
 - insulating material encapsulating chip and central lead ends, leaving the chip surface opposite the cavity and the peripheral lead ends unencapsulated; and
 - the unencapsulated peripheral lead ends bent into cantilevers for attachment to a horizontal substrate, the cantilevers having a geometry to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics.
2. The device of Claim 1, wherein the leadframe is selected from a group including copper, aluminum, alloys thereof, iron-nickel alloys, and Kovar™.
3. The device of Claim 2, wherein the unencapsulated peripheral lead ends have a geometry selected from a group including straight geometry, curved geometry, toroidal geometry, and multiple-bendings geometry.
4. The device of Claim 1, wherein the insulating material is a polymeric molding compound.
5. A packaged sensor microelectromechanical system (MEMS) device, comprising:
 - a semiconductor chip having a surface with a protected cavity containing a sensor, the cavity surrounded by solder bumps attached to the chip terminals, the bumped chip having a height;

a package including a housing and a leadframe integrated in the housing; the housing made of an insulating material shaped in small-outline configuration and having a central recess of a depth greater than the chip height; the leadframe having elongated leads with the central lead ends solderable, matching the chip solder bumps and positioned on the bottom of the recess, and the peripheral lead ends protruding from the housing;

the chip solder bumps attached to the leadframe so that the recess depth surpasses the bumped chip height; and

the protruding lead ends bent into cantilevers for attachment to a horizontal substrate, the cantilevers having a geometry to accommodate, under a force lying in the plane of the substrate, elastic bending and stretching beyond the limit of simple elongation based upon inherent material characteristics.

6. The device of Claim 5, wherein the protruding lead ends have a geometry selected from a group including straight geometry, curved geometry, toroidal geometry, and multiple bendings geometry.

7. The device of Claim 5, further including an iris attached over the recess, the iris operable to narrow an incoming radiation beam.

8. A method for fabricating a microelectromechanical system (MEMS) device, comprising the steps of:

providing a semiconductor chip having a surface with a protected cavity containing a sensor, the cavity surrounded by solder bumps attached to the chip terminals;

providing a leadframe having elongated leads, the central lead ends solderable and matching the chip solder bumps;

aligning the chip solder bumps on the central lead ends and reflowing the solder bumps, thereby attaching the chip to the leadframe;

encapsulating chip and central lead ends in an insulating material, leaving the chip surface opposite the cavity and the peripheral lead ends unencapsulated; and

bending the unencapsulated lead ends into spring-like cantilevers.

9. The method of Claim 8, wherein the step of encapsulating is a molding process using a polymeric compound.

10. The method of Claim 8, wherein the unencapsulated lead ends have a geometry selected from a group including straight geometry, curved geometry, toroidal geometry, and multiple bendings geometry.

11. A method for fabricating a microelectromechanical system (MEMS) device, comprising the steps of:

providing a semiconductor chip having a surface with a protected cavity containing a sensor, the cavity surrounded by solder bumps attached to the chip terminals, the bumped chip having a height;

providing a package including a housing and a leadframe integrated in the housing,

the housing made of an insulating material and having a central recess of a depth greater than the height of the bumped chip;

the leadframe having elongated leads with the central lead ends solderable, matching the chip solder bumps and positioned on the bottom of the recess, and the peripheral lead ends protruding from the housing and having a geometry selected from a group including straight geometry, curved geometry, toroidal geometry, and multiple bendings geometry;

aligning the chip solder bumps on the central lead ends;

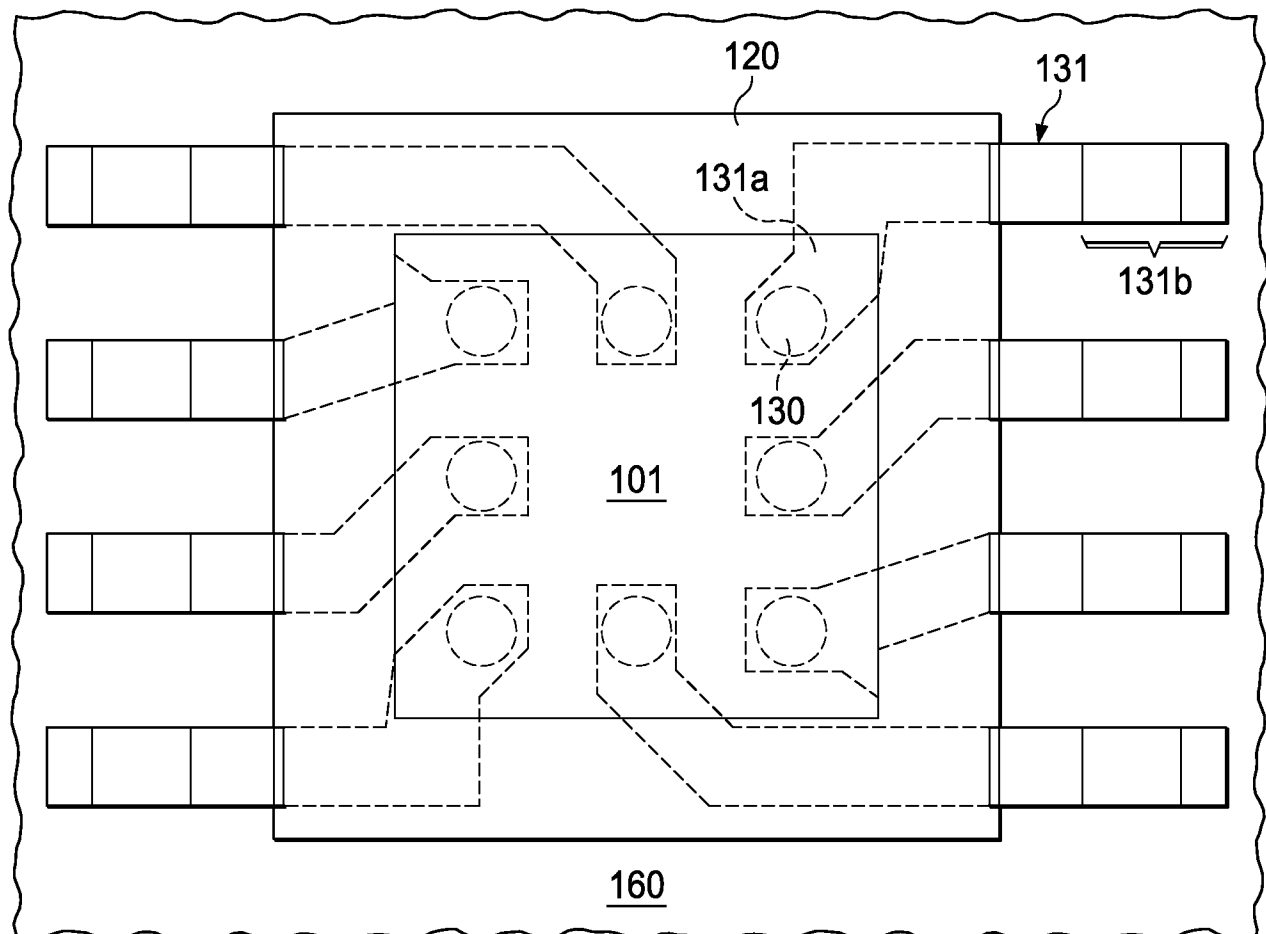
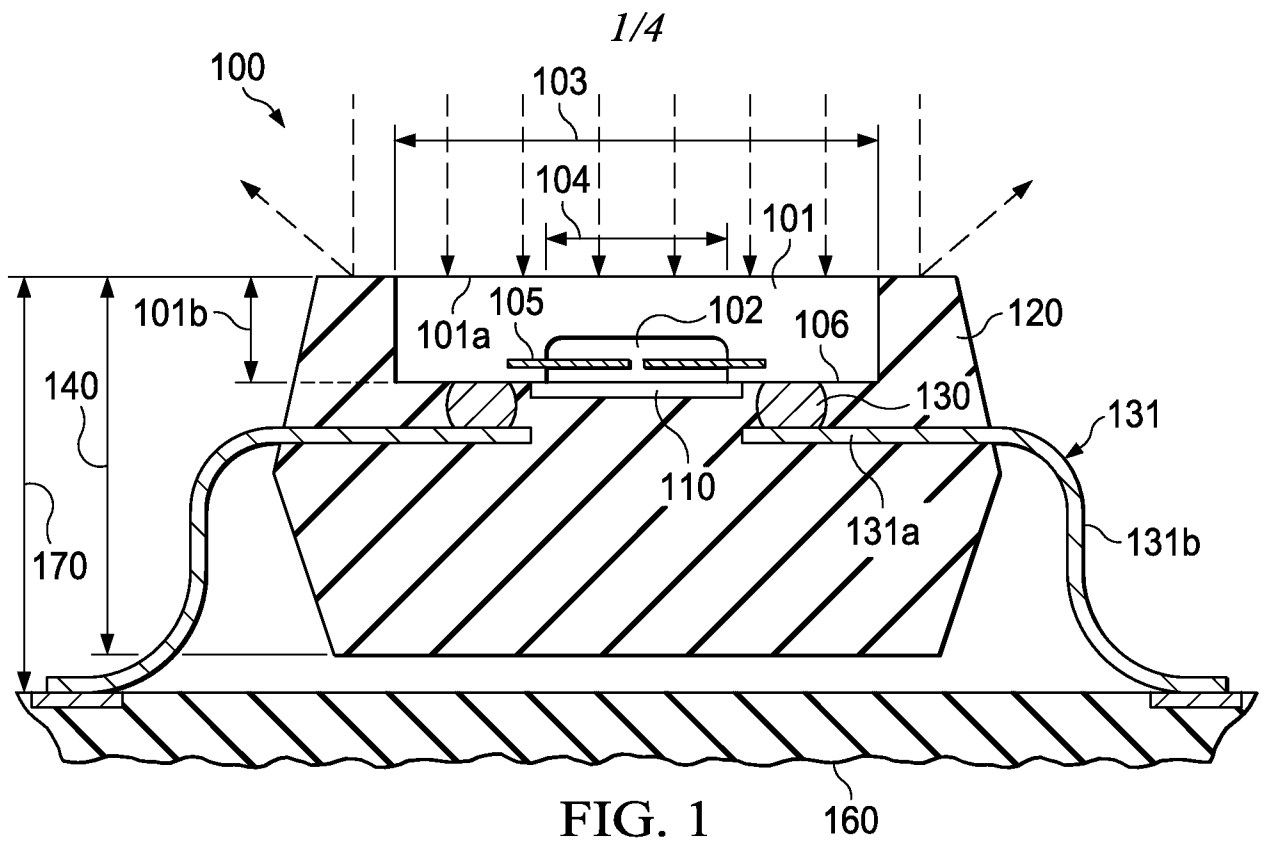
reflowing the solder bumps, thereby attaching the chip to the leadframe so that the recess depth surpasses the bumped chip height; and

bending the protruding lead ends into spring-like cantilevers.

12. The method of Claim 11, wherein the insulating material of the housing is a molding compound.

13. The method of Claim 11, wherein the housing is shaped in small-outline configuration.

14. The method of Claim 11, further including, after the step of reflowing, the step of attaching over the recess an iris narrowing an incoming radiation beam.



2/4

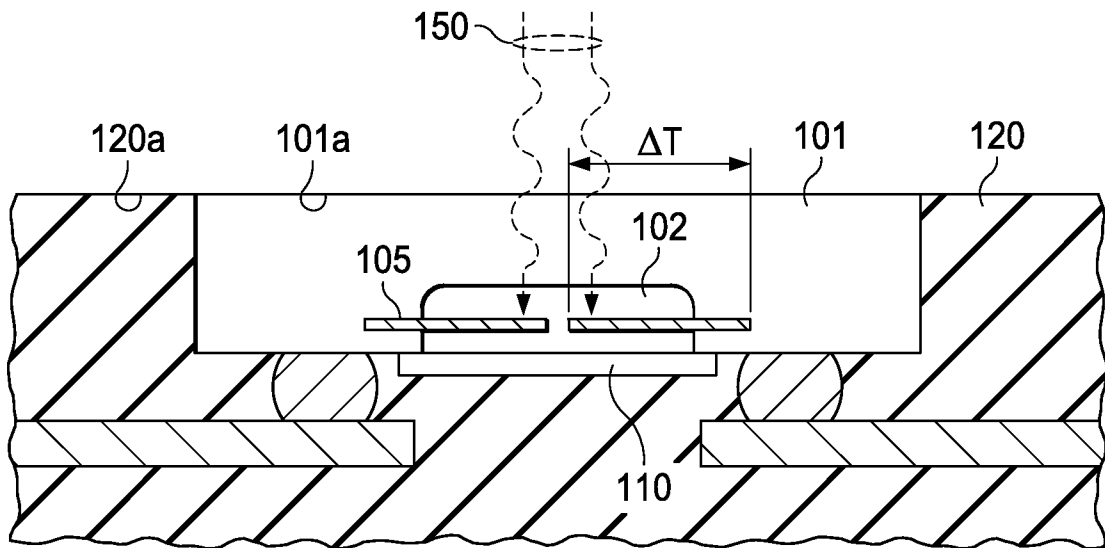


FIG. 2A

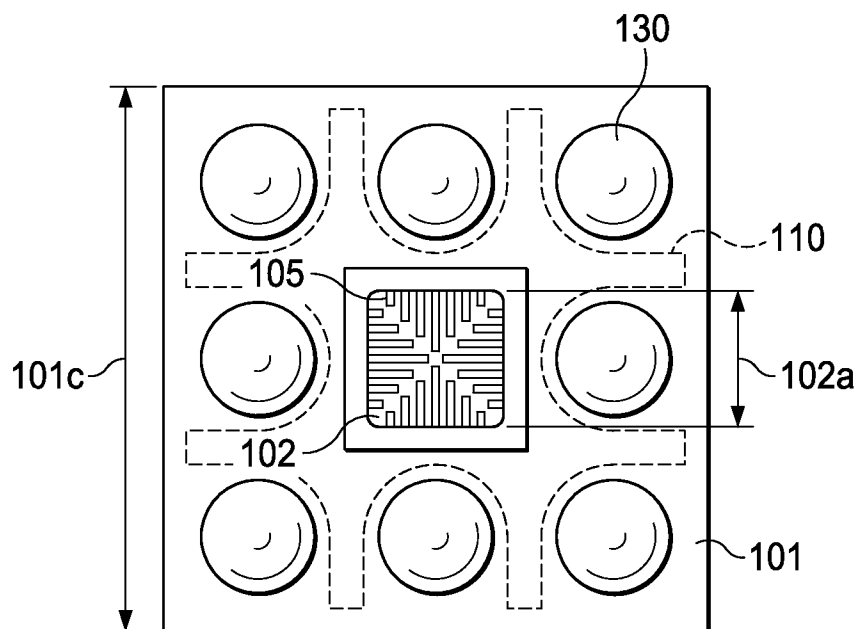


FIG. 2B

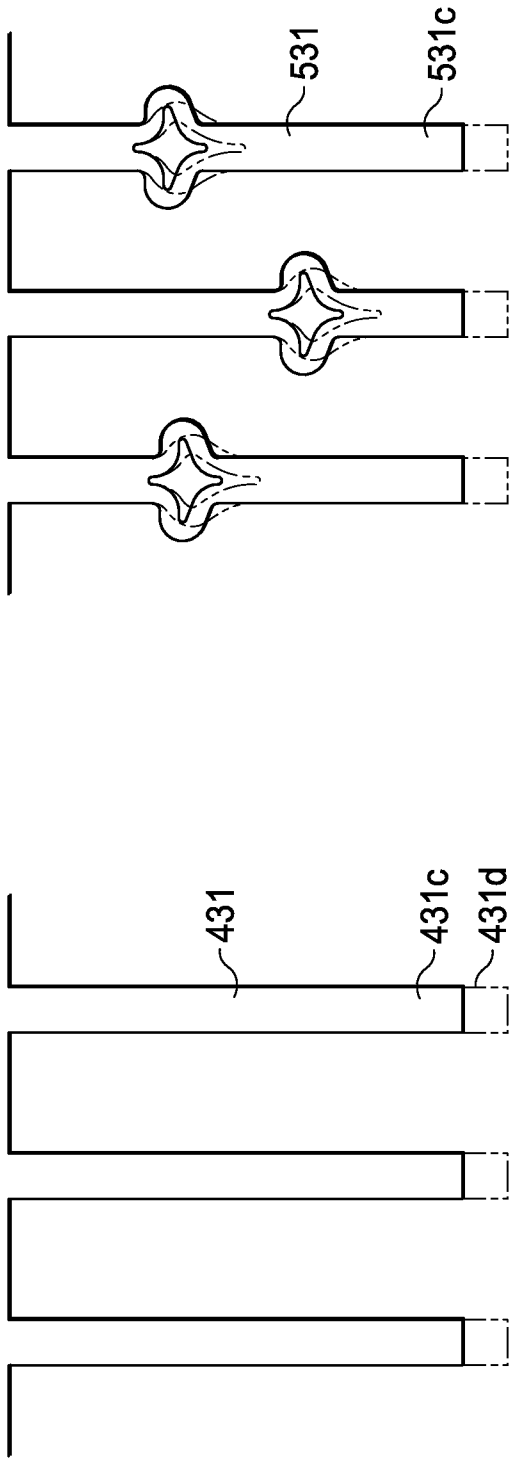


FIG. 5

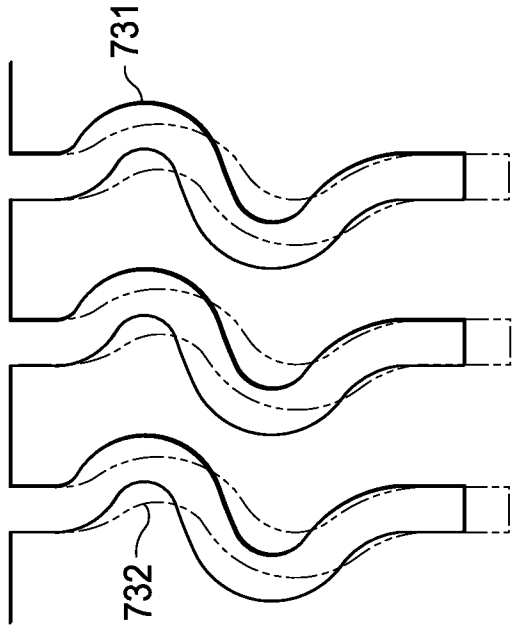
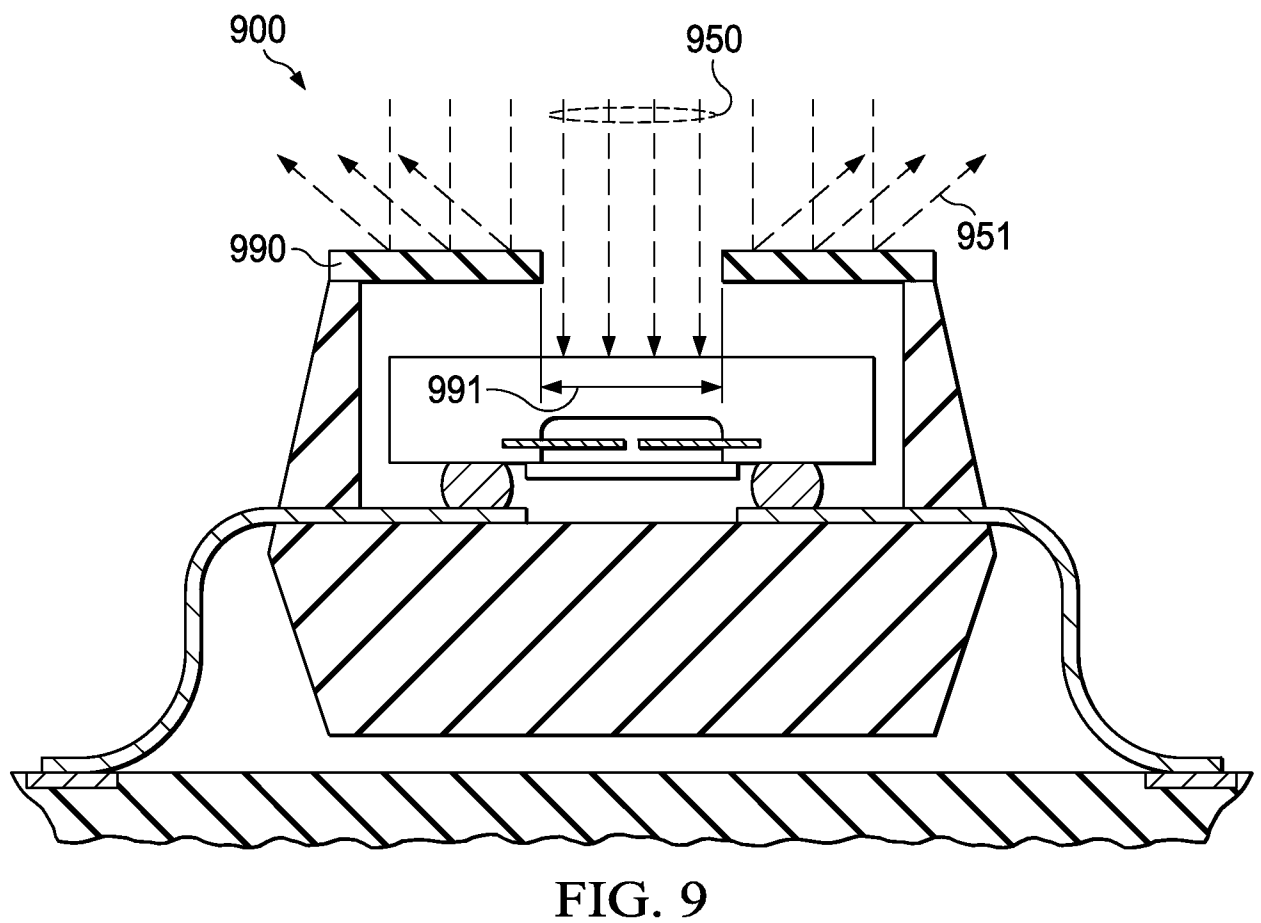
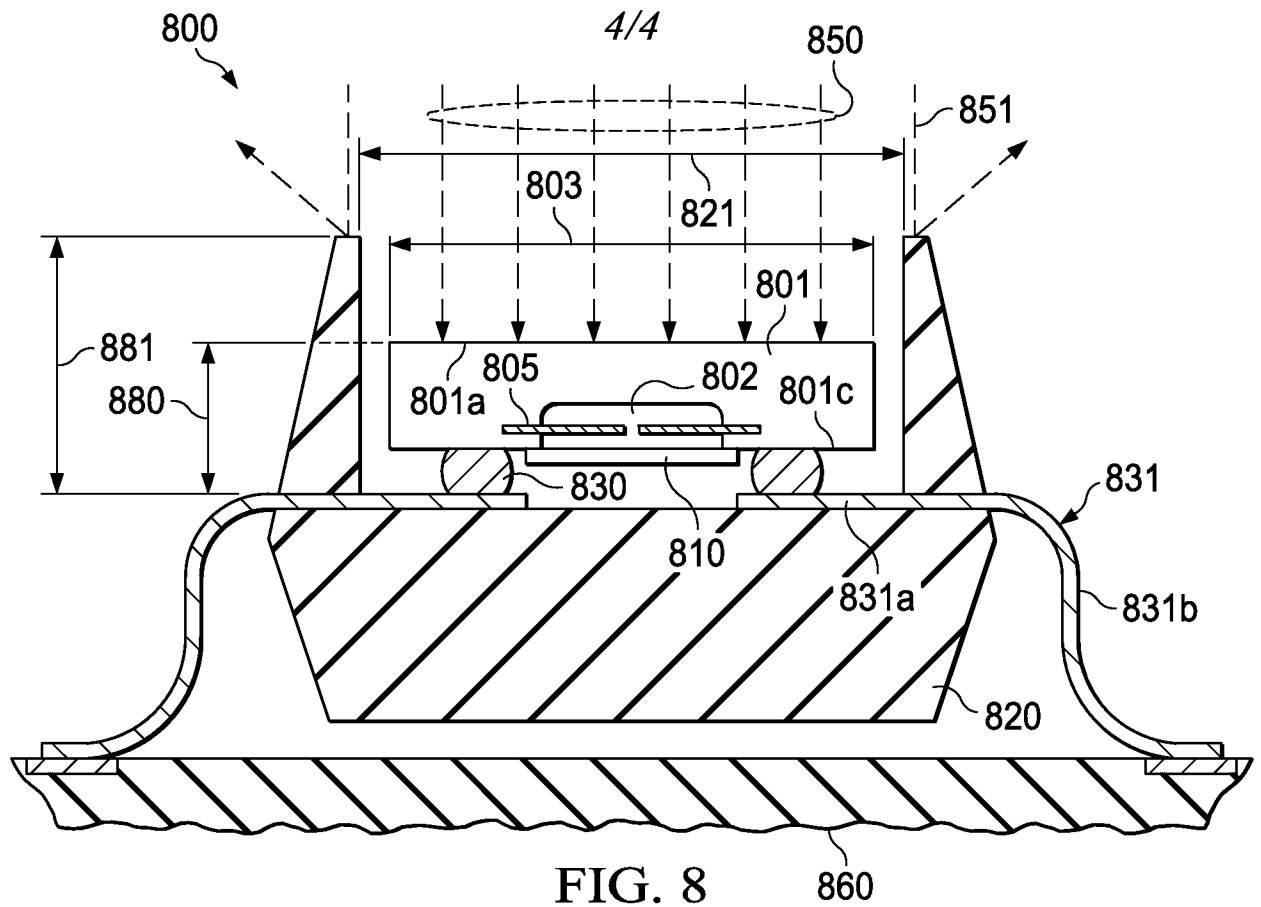


FIG. 6

FIG. 7



INTERNATIONAL SEARCH REPORT

International application No.
PCT/US2013/049516**A. CLASSIFICATION OF SUBJECT MATTER****B81B 7/00(2006.01)i, B81B 3/00(2006.01)i, H01L 23/00(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

B81B 7/00; H01L 21/60; H01L 41/04; H01L 23/48; H01L 2302; H02N 2/00; H01L 23/495; B81B 3/00; H01L 23/00

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & Keywords: leadframe, package, MEMS, thermal stress, and CTE

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	US 2012-0153446 A1 (JIANG, HUNT HANG) 21 June 2012 See abstract; paragraphs 11-14, 18 and figure 2.	1-4, 8-10
A		5-7, 11-14
Y	US 6072230 A (CARTER, JR. et al.) 06 June 2000 See abstract; column 5, line 17-column 6, line 6 and figures 1-2C.	1-14
Y	US 6828663 B2 (CHEN et al.) 07 December 2004 See abstract; column 3, lines 15-57 and figure 1.	5-7, 11-14
A	US 2004-0021402 A1 (MORLEY et al.) 05 February 2004 See abstract; paragraphs 63-65 and figures 4a, 6a.	1-14
A	US 5708293 A (OCHI et al.) 13 January 1998 See abstract; column 6, lines 15-58 and figure 1.	1-14



Further documents are listed in the continuation of Box C.



See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier application or patent but published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

28 October 2013 (28.10.2013)

Date of mailing of the international search report

29 October 2013 (29.10.2013)

Name and mailing address of the ISA/KR

Korean Intellectual Property Office
189 Cheongsu-ro, Seo-gu, Daejeon Metropolitan City,
302-701, Republic of Korea

Facsimile No. +82-42-472-7140

Authorized officer

AHN, Jae Yul

Telephone No. +82-42-481-8525



INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/US2013/049516

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
US 2012-0153446 A1	21/06/2012	CN 102522376 A CN 202352647 U TW 201240031 A US 8283758 B2	27/06/2012 25/07/2012 01/10/2012 09/10/2012
US 6072230 A	06/06/2000	EP 0902473 A2 EP 0902473 A3 JP 11-145362 A KR 10-1999-0029648 A TW 414981 A	17/03/1999 21/11/2001 28/05/1999 26/04/1999 11/12/2000
US 6828663 B2	07/12/2004	AU 2002-250249 A1 US 2002-0125553 A1 US 2005-0023663 A1 WO 02-073690 A2 WO 02-073690 A3	24/09/2002 12/09/2002 03/02/2005 19/09/2002 15/05/2003
US 2004-0021402 A1	05/02/2004	AT 431649 T AU 2003-234672 A1 DE 60327633 D1 EP 1535350 A2 EP 1535350 A4 EP 1535350 B1 IL 165327 A IL 165327 D0 JP 2005-528829 A US 6984925 B2 WO 0310-0876 A2 WO 0310-0876 A3	15/05/2009 12/12/2003 25/06/2009 01/06/2005 09/05/2007 13/05/2009 01/09/2009 15/01/2006 22/09/2005 10/01/2006 04/12/2003 29/01/2004
US 5708293 A	13/01/1998	JP 09-186286 A	15/07/1997